

TOSHIBA CMOS Digital Integrated Circuit Silicon Monolithic

# T C 7 M A 5 7 3 F K

Low-Voltage Octal D-Type Latch with 3.6 V Tolerant Inputs and Outputs

The TC7MA573FK is a high performance CMOS octal D-type latch. Designed for use in 1.8 V, 2.5 V or 3.3 V systems, it achieves high speed operation while maintaining the CMOS low power dissipation.

It is also designed with over voltage tolerant inputs and outputs up to 3.6 V.

This 8 bit D-type latch is controlled by a latch enable input (LE) and an output enable input ( $\overline{OE}$ ).

When the  $\overline{OE}$  input is high, the eight outputs are in a high impedance state.

All inputs are equipped with protection circuits against static discharge.



- Low voltage operation: VCC = 1.8~3.6 V
- High speed operation:  $t_{pd} = 4.2 \text{ ns} (\text{max}) (V_{CC} = 3.0 \sim 3.6 \text{ V})$ 
  - t<sub>pd</sub> = 4.7 ns (max) (V<sub>CC</sub> = 2.3~2.7 V) t<sub>pd</sub> = 9.4 ns (max) (V<sub>CC</sub> = 1.8 V)
- 3.6 V tolerant inputs and outputs.
- Output current:  $I_{OH}/I_{OL} = \pm 24 \text{ mA} \text{ (min)} (V_{CC} = 3.0 \text{ V})$ 
  - $I_{OH}/I_{OL} = \pm 18 \text{ mA} (min) (V_{CC} = 2.3 \text{ V})$
  - $IOH/IOL = \pm 6 \text{ mA} (min) (VCC = 1.8 \text{ V})$
- Latch-up performance: ±300 mA
- ESD performance: Machine model > ±200 Human body model > ±2000 V
- Package: VSSOP (US20)
- Power down protection is provided on all inputs and outputs.
- Supports live insertion/withdrawal (\*)
  - \*: To ensure the high-impedance state during power up or power down,  $\overline{OE}$  should be tied to V<sub>CC</sub> through a pullup resistor; the minimum value of the resistor is determined by the current-sourcing capability of the driver.

VSSOP20-P-0030-0.50

Weight: 0.03 g (typ.)

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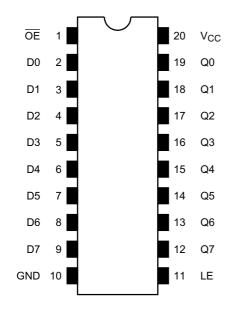
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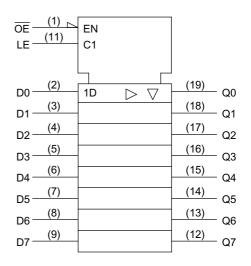
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# Pin Assignment (top view)



#### IEC Logic Level



#### Truth Table

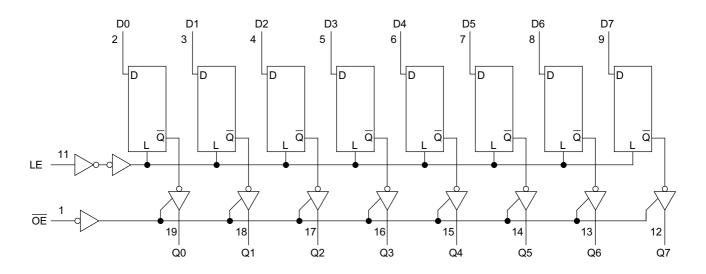
	Inputs					
ŌĒ	LE	D	Outputs			
Н	Х	Х	Z			
L	L	Х	Q <sub>n</sub>			
L	Н	L	L			
L	Н	Н	Н			

X: Don't care

Z: High impedance

Qn: Q outputs are latched at the time when the LE inputs is taken to a low logic level.

#### System Diagram



## **Maximum Ratings**

Characteristics	Symbol	Rating	Unit	
Power supply voltage	V <sub>CC</sub>	-0.5~4.6	V	
DC input voltage	V <sub>IN</sub>	-0.5~4.6	V	
DC output voltage	Vour	-0.5~4.6 (Note1)	V	
DC output voltage	Vout	-0.5~V <sub>CC</sub> + 0.5 (Note2)	v	
Input diode current	I <sub>IK</sub>	-50	mA	
Output diode current	I <sub>OK</sub>	±50 (Note3)	mA	
DC output current	IOUT	±50	mA	
Power dissipation	PD	180	mW	
DC V <sub>CC</sub> /ground current	I <sub>CC</sub> /I <sub>GND</sub>	±100	mA	
Storage temperature	T <sub>stg</sub>	-65~150	°C	

Note1: Off-state

Note2: High or low state. IOUT absolute maximum rating must be observed.

Note3:  $V_{OUT} < GND, V_{OUT} > V_{CC}$ 

#### **Recommended Operating Range**

Characteristics	Symbol	Rating	Unit
Supply voltage	Vee	1.8~3.6	V
Supply Voltage	V <sub>CC</sub> 1.8~3.6           1.2~3.6         (Note4)           V <sub>IN</sub> -0.3~3.6           V <sub>OUT</sub> 0~3.6         (Note5)           0~V <sub>CC</sub> (Note6)           ±24         (Note7)           IOH/IOL         ±18         (Note8)	v	
Input voltage	V <sub>IN</sub>	-0.3~3.6	V
	Vour	0~3.6 (Note5)	V
Output voltage	V001	0~V <sub>CC</sub> (Note6)	v
		±24 (Note7)	
Output current	I <sub>OH</sub> /I <sub>OL</sub>	±18 (Note8)	mA
		±6 (Note9)	
Operating temperature	T <sub>opr</sub>	-40~85	°C
Input rise and fall time	dt/dv	0~10 (Note10)	ns/V

Note4: Data retention only

Note5: Off-state

Note6: High or low state

Note7: V<sub>CC</sub> = 3.0~3.6 V

Note8: V<sub>CC</sub> = 2.3~2.7 V

Note9:  $V_{CC} = 1.8 V$ 

Note10:  $V_{IN} = 0.8 \sim 2.0 \text{ V}, V_{CC} = 3.0 \text{ V}$ 

#### **Electrical Characteristics**

## DC Characteristics (Ta = -40~85°C, 2.7 V < V<sub>CC</sub> $\leq$ 3.6 V)

Characte	riation	Symbol	Тор	t Condition		Min	Max	Unit
Character	IISUCS	Symbol			V <sub>CC</sub> (V)	IVIIII	Max	Unit
Input voltage	High level	VIH		—	2.7~3.6	2.0	_	V
input voltage	Low level	VIL		—	2.7~3.6	_	0.8	v
High level Output voltage			I <sub>OH</sub> = -100 μA	2.7~3.6	V <sub>CC</sub> - 0.2	—		
	V <sub>OH</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OH} = -12 \text{ mA}$	2.7	2.2	_		
				I <sub>OH</sub> = -18 mA	3.0	2.4	_	
				I <sub>OH</sub> = -24 mA	3.0	2.2	_	V
		Low level V <sub>OL</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 100 \ \mu A$	2.7~3.6		0.2	
				I <sub>OL</sub> = 12 mA	2.7		0.4	
	LOW level			I <sub>OL</sub> = 18 mA	3.0		0.4	
				I <sub>OL</sub> = 24 mA	3.0		0.55	
Input leakage curr	ent	I <sub>IN</sub>	V <sub>IN</sub> = 0~3.6 V		2.7~3.6		±5.0	μA
2 atoto output off	stata aurrant	1	$V_{IN} = V_{IH}$ or $V_{IL}$		2.7~3.6	_	±10.0	
3-state output off-state current I <sub>C</sub>		loz	V <sub>OUT</sub> = 0~3.6 V		2.7~3.0		±10.0	μA
Power off leakage	current	I <sub>OFF</sub>	V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		0		10.0	μA
Quiescent supply current	1	$V_{IN} = V_{CC}$ or GND		2.7~3.6		20.0		
	Icc	$V_{CC} \stackrel{\scriptstyle \leq}{=} (V_{IN},V_{OUT}) \stackrel{\scriptstyle \leq}{=}$	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 V$			±20.0	μA	
		Δlcc	$V_{IH} = V_{CC} - 0.6 V (p)$	er input)	2.7~3.6		750	

## DC Characteristics (Ta = $-40 \sim 85^{\circ}$ C, 2.3 V $\leq V_{CC} \leq 2.7$ V)

Character	istics	Symbol	Test	Condition	V <sub>CC</sub> (V)	Min	Max	Unit
Input voltage	High level	VIH	VIH—VIL—VIL—VOHVIN = VIH or VILIIVOLVIN = VIH or VILIINVIN = 0~3.6 VIOZVIN = VIH or VILVOUT = 0~3.6 V	_	2.3~2.7	1.6	_	V
Input voltage	Low level	VIL		_	2.3~2.7		0.7	v
High level Output voltage			I <sub>OH</sub> = -100 μA	2.3~2.7	V <sub>CC</sub> - 0.2	_		
	High level	V <sub>OH</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$	I <sub>OH</sub> = -6 mA	2.3	2.0	_	
	-			I <sub>OH</sub> = -12 mA	2.3	1.8	_	V
				I <sub>OH</sub> = -18 mA	2.3	1.7	_	
			$V_{IN} = V_{IH} \text{ or } V_{IL}$	$I_{OL} = 100 \ \mu A$	2.3~2.7	_	0.2	
	Low level	V <sub>OL</sub>		I <sub>OL</sub> = 12 mA	2.3	_	0.4	
				I <sub>OL</sub> = 18 mA	2.3	_	0.6	
Input leakage curre	ent	I <sub>IN</sub>	V <sub>IN</sub> = 0~3.6 V		2.3~2.7	_	±5.0	μA
2 atoto output off c	tata aurrant	1	$V_{IN} = V_{IH} \text{ or } V_{IL}$		2.3~2.7		±10.0	
3-state output off-state current		IOZ	V <sub>OUT</sub> = 0~3.6 V		2.3~2.1		±10.0	μA
Power off leakage	current	IOFF	V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		0	_	10.0	μA
Quiescent supply current		$V_{IN} = V_{CC}$ or GND	$V_{IN} = V_{CC}$ or GND		—	20.0	μA	
Quiescent supply (		Icc	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3$	3.6 V	2.3~2.7	_	±20.0	μΑ

# DC Characteristics (Ta = -40~85°C, 1.8 V $\leq$ V<sub>CC</sub> < 2.3 V)

Characteris	stics	Symbol	Test (	Test Condition		Min	Max	Unit
Input voltage	High level	VIH		_	1.8~2.3	$0.7 \times V_{CC}$	_	V
Input voltage	Low level	VIL		_	1.8~2.3	_	$0.2 \times V_{CC}$	v
	High level	Vон	$V_{IN} = V_{IH} \text{ or } V_{IL}$	I <sub>OH</sub> = -100 μA	1.8	V <sub>CC</sub> - 0.2	_	
Output voltage	0	0.1		I <sub>OH</sub> = -6 mA	1.8	1.4		V
	Low level	el Voi	$V_{IN} = V_{IH} \text{ or } V_{IL}$	I <sub>OL</sub> = 100 μA	1.8	_	0.2	
	LOWIEVEI	VOL		I <sub>OL</sub> = 6 mA	1.8	_	0.3	
Input leakage curren	nt	I <sub>IN</sub>	V <sub>IN</sub> = 0~3.6 V		1.8	_	±5.0	μA
3-state output off-sta	ate current	I <sub>OZ</sub>	$V_{IN} = V_{IH} \text{ or } V_{IL}$ $V_{OUT} = 0~3.6 \text{ V}$			_	±10.0	μA
Power off leakage c	urrent	I <sub>OFF</sub>	V <sub>IN</sub> , V <sub>OUT</sub> = 0~3.6 V		0	_	10.0	μA
Quiescent supply current			$V_{IN} = V_{CC}$ or GND		1.8	_	20.0	μA
Quescent Supply Ct		ICC	$V_{CC} \leq (V_{IN}, V_{OUT}) \leq 3.6 \text{ V}$		1.8	_	±20.0	μA

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# AC Characteristics (Ta = -40~85°C, Input: $t_r = t_f = 2.0 \text{ ns}$ , $C_L = 30 \text{ pF}$ , $R_L = 500 \Omega$ )

Characteristics	Symbol	Test Condition		Min	Max	Unit
	-		$V_{CC}(V)$			
	+		1.8	1.5	9.4	
Propagation delay time (D-Q)	t <sub>pLH</sub>	Figure 1, Figure 2	$2.5\pm0.2$	0.8	4.7	ns
	t <sub>pHL</sub>		$3.3\pm 0.3$	0.6	4.2	
			1.8	1.5	9.8	
Propagation delay time (LE-Q)	t <sub>pLH</sub>	Figure 1, Figure 2	$2.5\pm0.2$	0.8	4.9	ns
	t <sub>pHL</sub>		$3.3\pm0.3$	0.6	4.2	
			1.8	1.5	9.8	
3-state output enable time	t <sub>pZL</sub>	Figure 1, Figure 3	$2.5\pm0.2$	0.8	5.5	ns
	t <sub>pZH</sub>		$3.3\pm0.3$	0.6	4.5	
3-state output disable time	t <sub>pLZ</sub> t <sub>pHZ</sub>	Figure 1, Figure 3	1.8	1.5	6.5	ns
			$2.5\pm0.2$	0.8	3.6	
			$3.3\pm0.3$	0.6	3.3	
		Figure 1, Figure 2	1.8	4.0	_	ns
Minimum pulse width	t <sub>w (H)</sub>		$2.5\pm0.2$	1.5	_	
	. ,		$3.3\pm0.3$	1.5	_	
			1.8	2.5	_	ns
Minimum set-up time	ts	Figure 1, Figure 2	$2.5\pm0.2$	1.5	_	
			$3.3\pm0.3$	1.5		
			1.8	1.0		
Minimum hold time	t <sub>h</sub>	Figure 1, Figure 2	$2.5\pm0.2$	1.0		ns
			$3.3 \pm 0.3$	1.0	_	
			1.8		0.5	ns
Output to output skew	t <sub>osLH</sub>	(Note11)	2.5 ± 0.2	_	0.5	
· · · · · · · · · · · · · · · · · · ·	t <sub>osHL</sub>	(	$3.3 \pm 0.3$	_	0.5	

For  $C_L = 50 \text{ pF}$ , add approximately 300 ps to the AC maximum specification.

Note11: This parameter is guaranteed by design.  $(t_{OSLH} = |t_{pLHm} - t_{pLHn}|, \ t_{OSHL} = |t_{pHLm} - t_{pHLn}|)$ 

## Dynamic Switching Characteristics (Ta = 25°C, Input: $t_r = t_f = 2.0 \text{ ns}$ , $C_L = 30 \text{ pF}$ )

Characteristics	Symbol	Test Condition		V <sub>CC</sub> (V)	Тур.	Unit
		$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note12)	1.8	0.25	
Quiet output maximum dynamic $V_{OL}$	V <sub>OLP</sub>	$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note12)	2.5	0.6	V
		$V_{IH}=3.3~V,~V_{IL}=0~V$	(Note12)	3.3	0.8	
	V <sub>OLV</sub>	$V_{IH} = 1.8 V, V_{IL} = 0 V$	(Note12)	1.8	-0.25	v
Quiet output minimum dynamic $V_{OL}$		$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note12)	2.5	-0.6	
		$V_{IH} = 3.3 \text{ V}, \text{ V}_{IL} = 0 \text{ V}$	(Note12)	3.3	-0.8	
		$V_{IH} = 1.8 \text{ V}, V_{IL} = 0 \text{ V}$	(Note12)	1.8	1.5	
Quiet output minimum dynamic $V_{OH}$	VOHV	$V_{IH} = 2.5 V, V_{IL} = 0 V$	(Note12)	2.5	1.9	V
		$V_{IH} = 3.3 \text{ V}, V_{IL} = 0 \text{ V}$	(Note12)	3.3	2.2	

Note12: This parameter is guaranteed by design.

#### **Capacitive Characteristics (Ta = 25°C)**

Characteristics	Symbol	Test Condition			
Characteristics	Symbol	rest condition	$V_{CC}(V)$	Тур.	Unit
Input capacitance	C <sub>IN</sub>	_	1.8, 2.5, 3.3	6	pF
Output capacitance	CO		1.8, 2.5, 3.3	7	pF
Power dissipation capacitance	C <sub>PD</sub>	$f_{IN} = 10 \text{ MHz}$ (Note13)	1.8, 2.5, 3.3	20	pF

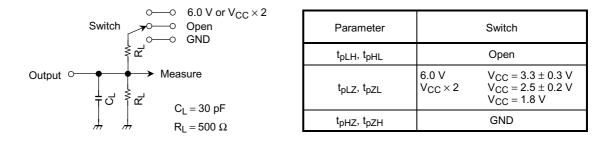
Note13: C<sub>PD</sub> is defined as the value of the internal equivalent capacitance which is calculated from the operating current consumption without load.

Average operating current can be obtained by the equation:

 $I_{CC (opr)} = C_{PD}KV_{CC}Kf_{IN} + I_{CC}/8$  (per bit)

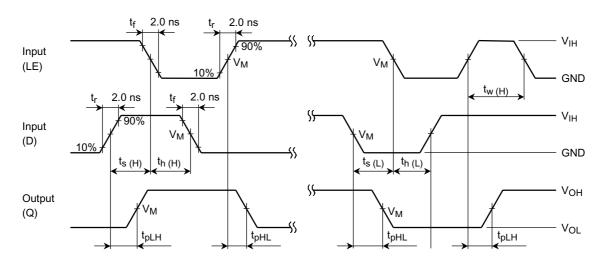
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#### **AC Test Circuit**



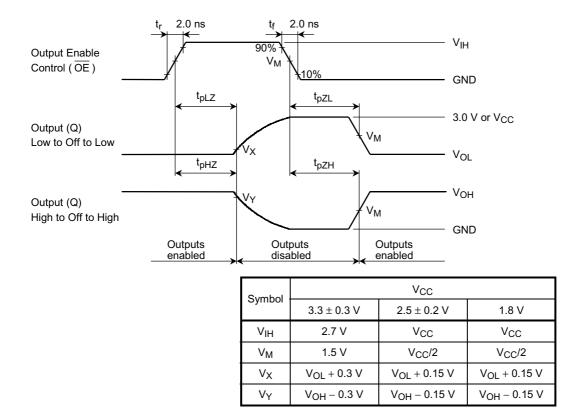


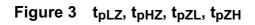
#### **AC Waveform**



 $\label{eq:Figure 2} \quad t_{pLH},\,t_{pHL},\,t_w,\,t_s,\,t_h$ 

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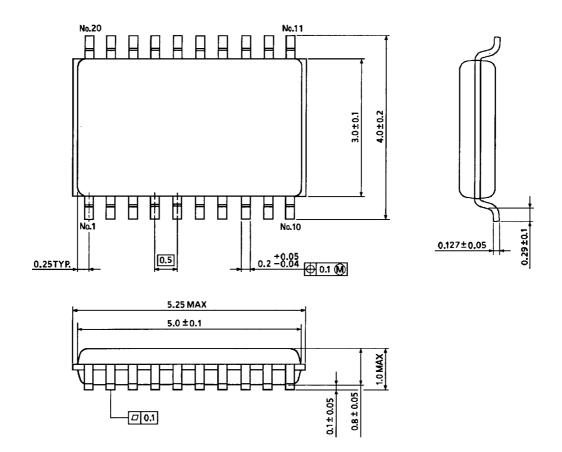




#### **Package Dimensions**

VSSOP20-P-0030-0.50

Unit : mm



Weight: 0.03 g (typ.)